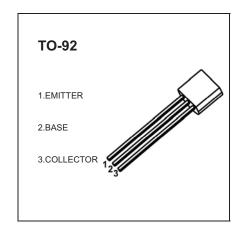


## JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

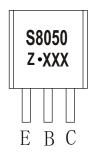
## **TO-92 Plastic-Encapsulate Transistors**

# \$8050 TRANSISTOR (NPN) FEATURES

- Complimentary to S8550
- Collector current: I<sub>C</sub>=0.5A



#### **MARKING**



S8050=Device code

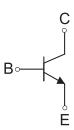
Solid dot=Green molding compound device,

if none,the normal device

Z=Rank of hfe,

XXX=Code

#### **Equivalent Circuit**



#### ORDERING INFORMATION

	Part Number	Package	Packing Method	Pack Quantity
	S8050	TO-92	Bulk	1000pcs/Bag
ſ	S8050-TA	TO-92	Tape	2000pcs/Box

#### MAXIMUM RATINGS (T₂=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	0.5	А
P <sub>D</sub>	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	°C /W
Tj	Junction Temperature	150	℃
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

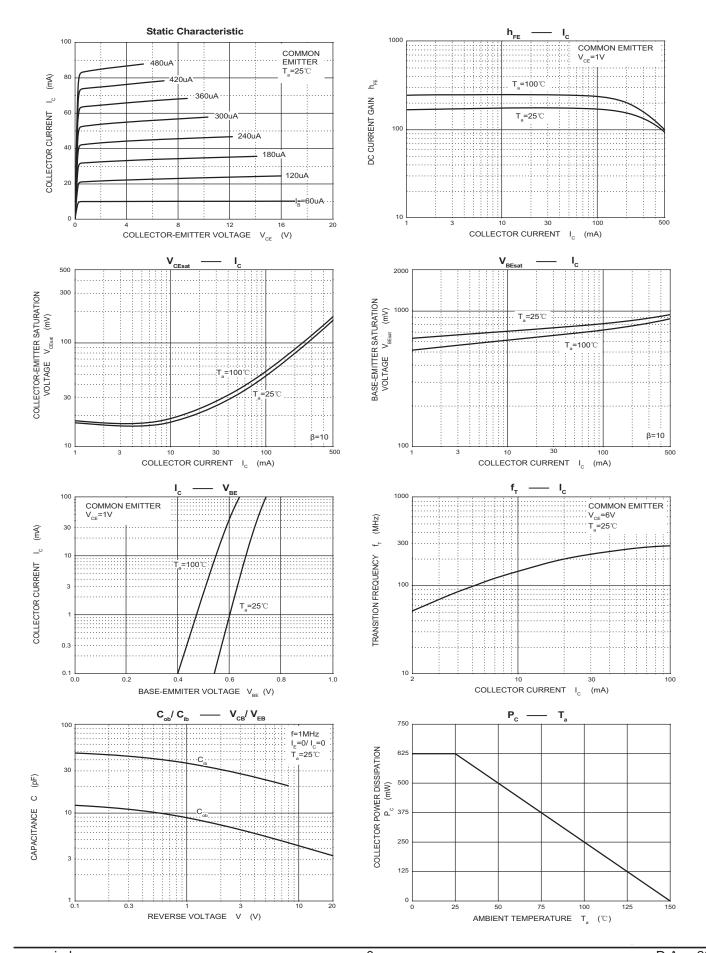
## **ELECTRICAL CHARACTERISTICS**

## $T_a$ =25 $^{\circ}$ C unless otherwise specified

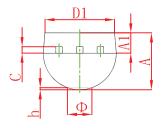
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 100μA, I <sub>E</sub> =0	40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 0.1mA, I <sub>B</sub> =0	25			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 100μΑ, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40 V , I <sub>E</sub> =0			0.1	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = 20 V , I <sub>B</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> =0			0.1	μA
DC ourrent goin	h <sub>FE(1)</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 50mA	85		400	
DC current gain	h <sub>FE(2)</sub>	V <sub>CE</sub> = 1V, I <sub>C</sub> = 500mA	50			
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			0.6	V
Base-emitter saturation voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1.2	V
Transition frequency	f⊤	V <sub>CE</sub> = 6V, I <sub>C</sub> =20mA f =30MHz	150			MHz

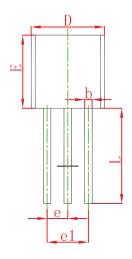
## CLASSIFICATION OF h<sub>FE(1)</sub>

Rank	В	С	D	D3
Range	85-160	120-200	160-300	300-400



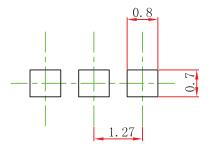
## **TO-92 Package Outline Dimensions**





Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	3.300	3.700	0.130	0.146	
A1	1.100	1.400	0.043	0.055	
b	0.380	0.550	0.015	0.022	
С	0.360	0.510	0.014	0.020	
D	4.300	4.700	0.169	0.185	
D1	3.430		0.135		
E	4.300	4.700	0.169	0.185	
е	1.27	1.270 TYP		) TYP	
e1	2.440	2.640	0.096	0.104	
L	14.100	14.500	0.555	0.571	
Ф		1.600		0.063	
h	0.000	0.380	0.000	0.015	

## **TO-92 Suggested Pad Layout**



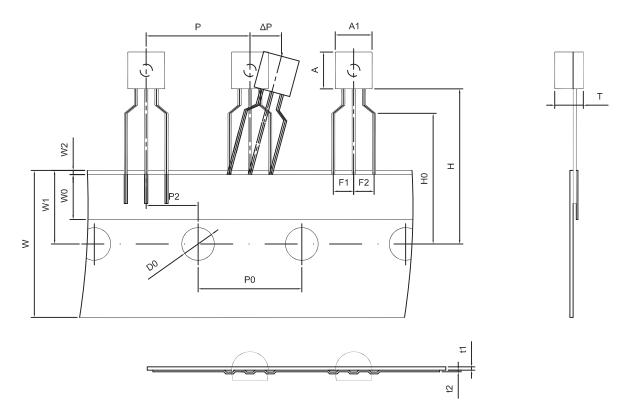
#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

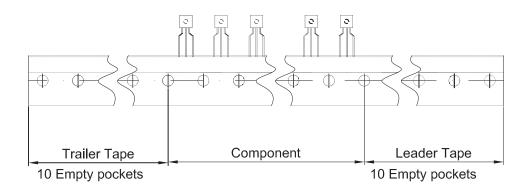
#### NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

## **TO-92 PACKAGE TAPEING DIMENSION**



Dimiensions are in millimeter								
A1 A T P P0 P2 F1 F2 W							W	
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	Н	H0	D0	t1	t2	ΔΡ
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Вох	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250